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Docket No.: 61352-075

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| In re Application of | : | Customer Number: 20277 |
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| Nobuyuki OTSUKA, et al. | : | Confirmation Number: 2226 |
| | : | |
| Serial No.: 10/817,035 | : | Group Art Unit: 2811 |
| | : | |
| Filed: April 05, 2004 | : | Examiner: Not Yet Assigned |
| | : | |
| For: | : | A GALLIUM INDIUM NITRIDE ARSENIDE BASED EPITAXIAL WAFER, A HETERO FIELD EFFECT TRANSISTOR USING THE WAFER, AND A METHOD OF FABRICATING THE HETERO FIELD EFFECT TRANSISTOR |

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

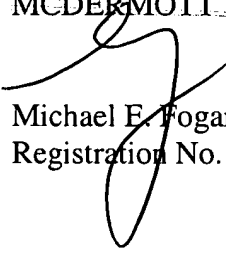
10/817,035

Each non-English language reference was first cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the international search report is attached for the Examiner's information

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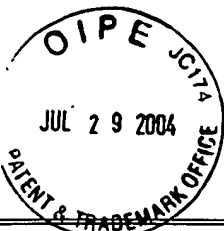
Respectfully submitted,

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Date: July 29, 2004



SHEET 1 OF 1

| INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449) | | | | ATTY. DOCKET NO. 61352-075 | | SERIAL NO. 10/817,035 | |
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| | | | | APPLICANT Nobuyuki OTSUKA, et al. | | | |
| | | | | FILING DATE April 05, 2004 | | GROUP 2811 | |
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| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Code ² (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | | |
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| | | WANG, Jyh-Shyang et al., "Growth of InAsn/InGaAs (P) quantum wells on InP by gas source molecular beam epitaxy", <i>Journal of Vacuum Science & Technology B</i> , Vol. 19, No. 1 January/February 2001, pp 202-206 | | | | | |
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| EXAMINER | | | | DATE CONSIDERED | | | |

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